Diode Semiconductor Device - Page 1 of 1



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Inclosure Ma	iterial:
Metal	
Overall Leng	ith:
0.560 inches	
Terminal Ler	ngth:
1.250 inches	
Overall Diam	neter:
0.235 inches	
Function For	r Which Designed:
Transient sup	pressor
Joint Electro	nic Device Engineering Council/jedec/case Outline Designation:
Do-13	
Electrode Inf	ernally-electrically Connected To Case:
Cathode	
Mounting Me	ethod:
Terminal	
Semiconduc	tor Material:
Silicon	
Voltage Rati	ng In Volts Per Characteristic:
760.0 breakc	lown voltage, dc
Current Rati	ng Per Characteristic:
200.00 ampe	res forward current, average preset
Power Rating	g Per Characteristic:
3.0 watts sma	all-signal input power, common-collector absolute
Maximum O	perating Tempurature Per Measurement Point:
175.0 degree	s celsius ambient air
Test Data Do	ocument:
05869-72072	0 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc
excludes any	specification, standard or other document that may be referenced in a basic governing drawing)
Terminal Typ	be And Quantity:
2 uninsulated	wire lead
Shelf Life:	
N/a	
Unit Of Meas	sure:
Demilitarizat	ion:
No	
Fiig:	
A110a0	